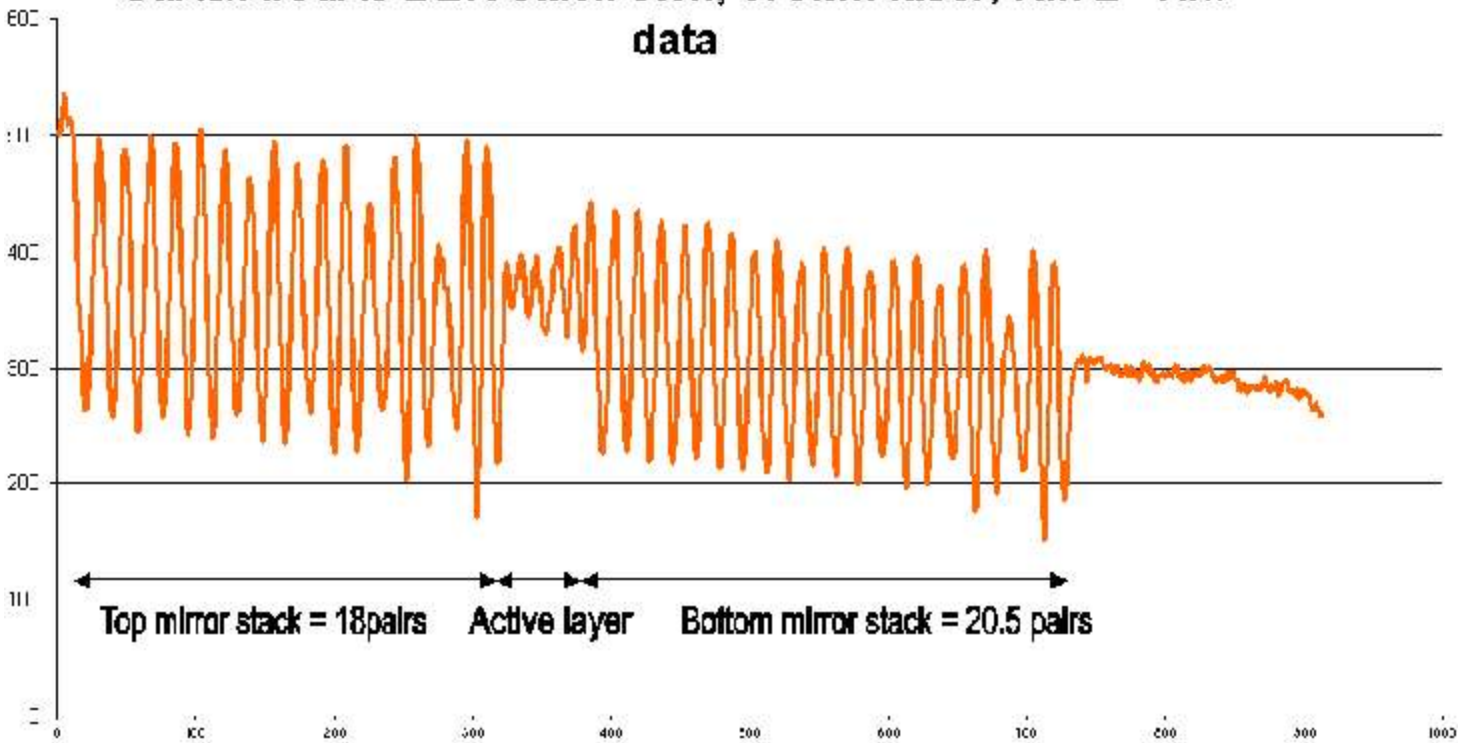


Plasmalab Data

Laser Interferometry: GaAs/AlGaAs DBR ICP Etching

GaAs/AlGaAs DBR stack etch, 675nm laser, run 2 - raw data



Chlorine based Process
 Rate : > 0.3 $\mu\text{m}/\text{min}$
 Selectivity to SiO_2 > 10:1, to resist > 5:1
 good uniformity
 anisotropic profile
 smooth sidewalls
 clean etch surface

time (secs) *Plasmalab 80 Plus*

Plasmalab System 100/ 133

Distributed Bragg Reflector:
 SEM's from OPT application lab
 in Yatton, UK

